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## **REDW 2015 Table of Contents**

<b>Heavy Ion Single Event Effects Measurements of Xilinx Zynq-7000 FPGA .....</b>	<b>1</b>
<i>Mehran Amrbar, Farokh Irom, Steven M. Guertin and Greg Allen, Jet Propulsion Laboratory, USA</i>	
<b>Neutron SEE testing of the 65nm SmartFusion2 Flash-Based FPGA.....</b>	<b>5</b>
<i>Durwyn Dsilva, Jih-Jong Wang, Nadia Rezzak and Narayan Jat, Microsemi, USA</i>	
<b>Heavy-Ion Induced SETs in 32nm SOI Inverter Chains .....</b>	<b>10</b>
<i>Jeffrey A. Maharrey, Jeffrey S. Kauppila, Rachel C. Quinn, Vanderbilt University, USA; T. Daniel Loveless, University of Tennessee at Chattanooga, USA; En Xia Zhang, W. Timothy Holman, Bharat L. Bhuva and Lloyd W. Massengill, Vanderbilt University, USA</i>	
<b>Impact of Temperature and Vcc Variation on 20nm Kintex UltraScale FPGAs Neutron Soft Error Rate .....</b>	<b>15</b>
<i>Pierre Maillard, Michael Hart, Jeff Barton, Praful Jain and James Karp, Xilinx Inc., USA</i>	
<b>SEE Testing of the Intersil ISL71840SEH 16-channel Analog Multiplexer .....</b>	<b>20</b>
<i>N. W. van Vonno, L. G. Pearce, K. S. Bernard and E. J. Thomson, Intersil, USA</i>	
<b>SET and SEFI characterization of the 65 nm SmartFusion2 flash-based FPGA under heavy ion irradiation.....</b>	<b>25</b>
<i>Nadia Rezzak, Durwyn Dsilva, Jih-Jong Wang and Narayan Jat, Microsemi, USA</i>	
<b>Heavy Ions Induced Single Event Upsets Testing of the 28 nm Xilinx Zynq-7000 All Programmable SoC .....</b>	<b>29</b>
<i>Lucas Antunes Tambara, Fernanda Lima Kastensmidt, Universidade Federal do Rio Grande do Sul (UFRGS), Brazil; Nilberto H. Medina, Nemitala Added, Vitor A. P. Aguiar, Fernando Aguirre, Eduardo L. A. Macchione, Universidade de São Paulo (USP), Brazil; and Marcilei A. G. Silveira, Centro Universitário da FEI, Brazil</i>	
<b>Radiation Effects Characterization of a 3.125Gbps 90nm SerDes IP .....</b>	<b>35</b>
<i>Anthony Wilson, Sasko Zarev and Mark Kazmier, Aeroflex, USA</i>	
<b>Heavy Ion SEU Test Data for 32nm SOI Flip-Flops .....</b>	<b>40</b>
<i>R. C. Quinn, J. S. Kauppila, Vanderbilt University, USA; T. D. Loveless, University of Tennessee at Chattanooga, USA; J. A. Maharrey, J. D. Rowe, M. W. McCurdy, E. X. Zhang, M. L. Alles, B. L. Bhuva, R. A. Reed, W. T. Holman, Vanderbilt University, USA; M. Bounasser, K. Lilja, Robust Chip Inc., USA; and L. W. Massengill, Vanderbilt University, USA</i>	
<b>Compendium of Current Single Event Effects for Candidate Spacecraft Electronics for NASA .....</b>	<b>45</b>
<i>Martha V. O'Bryan, AS&amp;D, Inc. USA; Kenneth A. LaBel, Dakai Chen, Michael J. Campola, Megan C. Casey, Jean Marie Lauenstein, Jonathan A. Pellish, Raymond L. Ladbury, NASA GSFC, USA; and Melanie D. Berg, AS&amp;D, Inc. USA</i>	
<b>2015 Compendium of Recent Test Results of Single Event Effects Conducted by the Jet Propulsion Laboratory's Radiation Effects Group .....</b>	<b>54</b>
<i>Gregory R. Allen, Leif Z. Scheick, Farokh Irom, Steven M. Guertin, Philippe C. Adell, Mehran Amrbar, Sergeh Vartanian and Michael O'Connor, JPL, USA</i>	
<b>Compendium of Current Total Ionizing Dose and Displacement Damage for Candidate Spacecraft Electronics for NASA .....</b>	<b>67</b>
<i>Michael J. Campola, NASA GSFC, USA; Donna J. Cochran, ASRC Federal Space and Defense, Inc. (AS&amp;D, Inc.), USA; Alvin J. Boutte, Dakai Chen, NASA GSFC, USA; Robert A. Gigliuto, ASRC Federal Space and Defense, Inc. (AS&amp;D, Inc.), USA; Kenneth A. LaBel, Jonathan A. Pellish, Raymond L. Ladbury, Megan C. Casey, NASA GSFC, USA; Edward P. Wilcox, ASRC Federal Space and Defense, Inc. (AS&amp;D, Inc.), USA; Martha V. O'Bryan, Jean-Marie Lauenstein, Dan Violette and Michael A. Xapsos, NASA GSFC, USA</i>	
<b>Single Event Upset Characterization of the Zynq-7000 ARM® Cortex™-A9 Processor Unit Using Proton Irradiation ....</b>	<b>76</b>
<i>David M. Hiemstra and Valeri Kirischian, MDA, Canada</i>	
<b>Guide to the 2014 IEEE Radiation Effects Data Workshop Record.....</b>	<b>79</b>
<i>David M. Hiemstra, MDA, Canada</i>	

<b>Predicting Optocoupler Life with Radiation Damage in Various Circuits.....</b>	<b>87</b>
<i>J. Brelska and D. M. Hiemstra, MDA, Canada</i>	
<b>Floating Gate Dosimeter Measurements at 4M Lunar Flyby Mission .....</b>	<b>93</b>
<i>J. Cesari, A. Barbancho, A. Pineda, Integrated Circuits Malaga SL, Spain; G. Ruy and H. Moser, LuxSpace Sarl, Luxembourg</i>	
<b>Total Ionizing Dose Radiation Effects on 14 nm FinFET and SOI UTBB Technologies .....</b>	<b>97</b>
<i>Harold Hughes, Patrick McMarr, NRL, USA; Michael Alles, Enxia Zhang, Charles Arutt, Vanderbilt University, USA; Bruce Doris, Derrick Liu, Richard Southwick and Philip Oldiges, IBM, USA</i>	
<b>Electrical mode influence on TID sensitivity of integrated and hybrid DC-DC converters .....</b>	<b>103</b>
<i>Leonid N. Kessarinskiy, Dmitry V. Boychenko and Alexey Y. Borisov, National Research Nuclear University (NRNU MEPhI), Moscow, Russian Federation</i>	
<b>Proton and Heavy Ion Sensitivity of Commercial Reference Voltage and Voltage Regulator Devices .....</b>	<b>107</b>
<i>R. Koga, S. Bielat, J. George and S. Davis, Aerospace, USA</i>	
<b>Terrestrial Neutron Induced Failures in Commercial SiC Power MOSFETs at 27C and 150C.....</b>	<b>115</b>
<i>A. Akturk, CoolCAD Electronics LLC, USA; R. Wilkins, Prairie View A&amp;M University, USA; and J. McGarry, CoolCAD Electronics LLC, USA</i>	
<b>Leakage Current Degradation of Gallium Nitride Transistors Due to Heavy Ion Tests .....</b>	<b>120</b>
<i>Brian D. Olson, J. David Ingalls, Casey H. Rice, Casey C. Hedge, Patrick L. Cole, Adam R. Duncan and Sarah E. Armstrong, Naval Surface Warfare Center, Crane Division, USA</i>	
<b>Heavy Ion Testing of Commercial GaN Transistors in the Radio Frequency Spectrum.....</b>	<b>130</b>
<i>Sarah E. Armstrong, NSWC Crane, USA; Ken Bole, Holly Bradley, Ethan Johnson, James Staggs, Walter Shedd, Air Force Research Lab, USA; Patrick L. Cole, Casey H. Rice, J. David Ingalls, Casey C. Hedge, Adam R. Duncan and Brian D. Olson, NSWC Crane, USA</i>	
<b>Ionizing Radiation Effects in Non-Radiation-Tolerant Commercial Video Cameras.....</b>	<b>136</b>
<i>Eli Simova and Paul A. Rochefort, Canadian Nuclear Laboratories, Canada</i>	
<b>Test Results Obtained on the Low and High Energies Heavy Ion Test Facilities.....</b>	<b>142</b>
<i>Vasily S. Anashin, Aleksandr E. Koziukov, Linaris R. Bakirov, Timofey A. Maksimenko, Alexander I. Ozerov, Grigory A. Protopopov, Branch of JCS URSC-ISDE, Russian Federation; and Pavel A. Chubunov, Branch of URSC - ISDE, Russian Federation</i>	
<b>Vanderbilt Pelletron - Low Energy Protons and Other Ions for Radiation Effects on Electronics.....</b>	<b>146</b>
<i>Michael W. McCurdy, Marcus H. Mendenhall, Robert A. Reed, Bridget R. Rogers, Robert A. Weller and Ronald D. Schrimpf, Vanderbilt University, USA</i>	
<b>Radiation Test Results for Common CubeSat Microcontrollers and Microprocessors.....</b>	<b>152</b>
<i>Steven M. Guertin, Mehran Amrbar and Sergeh Vartanian, JPL/Caltech, USA</i>	
<b>Radiation Evaluation of Ferroelectric Random Access Memory Embedded in 180nm CMOS Technology .....</b>	<b>161</b>
<i>B. A. Dahl, J. Cruz-Colon, R. C. Baumann, J. A. Rodriguez, C. Zhou, J. Rodriguez-Latorre, S. Khan, T. San and T. Trinh, Texas Instruments, USA</i>	
<b>Single Event Effects in COTS Ferroelectric RAM Technologies .....</b>	<b>167</b>
<i>Zhangang Zhang, Science and Technology on Reliability Physics and Application of Electronic Component Laboratory, China Electronic Product Reliability and Environmental Testing Research Institute (CEPREI) and South China University of Technology, China; Zhifeng Lei, Science and Technology on Reliability Physics and Application of Electronic Component Laboratory, China Electronic Product Reliability and Environmental Testing Research Institute (CEPREI), China; Zhenlei Yang, Xiaohui Wang, Bin Wang, Jie Liu, Institute of Modern Physics, Chinese Academy of Sciences, China; Yunfei En, Hui Chen, Science and Technology on Reliability Physics and Application of Electronic Component Laboratory, China Electronic Product Reliability and Environmental Testing Research Institute (CEPREI), China; and Bin Li, South China University of Technology, China</i>	

<b>Heavy Ion Single Event Effects Measurements of 512Mb ISSI SDRAM .....</b>	<b>172</b>
<i>Farokh Irom and Mehran Amrbar, Jet Propulsion Laboratory, United States</i>	
<b>Proton Displacement Damage Measurements in Commercial Optocouplers.....</b>	<b>178</b>
<i>Farokh Irom, Gregory R. Allen and Bernard G. Rax, Jet Propulsion Laboratory, United States</i>	
<b>Compendium of Single-Event Latchup and Total Ionizing Dose Test Results of Commercial Digital to Analog Converters.....</b>	<b>183</b>
<i>Farokh Irom and Shri G. Agarwal, Jet Propulsion Laboratory, United States</i>	
<b>Low Dose Rate testing of ADXL327 Accelerometer for a Mars Mission .....</b>	<b>191</b>
<i>M. Álvarez, J. J. Jiménez, D. Escribano, P. Manzano, I. Arruego, V. Apéstigue, M. González-Guerrero, I. Martín, INTA, Spain; and D. M. González-Castaño, USC, Spain</i>	
<b>ELDRS Characterization up to 300 krad of Texas Instruments High Speed Amplifiers, LM7171 and LM6172 .....</b>	<b>194</b>
<i>Kirby Kruckmeyer and Thang Trinh, Texas Instruments, USA</i>	
<b>Experimental Investigation of SELs in SiT8003 MEMS-Oscillators .....</b>	<b>199</b>
<i>Alexander S. Tararaksin, Leonid N. Kessarinskiy, Alexander A. Pechenkin, Alexandra V. Demidova, Andrey V. Yanenko, Dmitry V. Boychenko and Alexander Y. Nikiforov, National Research Nuclear University MEPhI (Moscow Engineering Physics Institute), Moscow, Russian Federation</i>	
<b>Preliminary Radiation Testing of a State-of-the-Art Commercial 14nm CMOS Processor / System-on-a-Chip .....</b>	<b>203</b>
<i>Carl M. Szabo, Jr., AS&amp;D, Inc. (GSFC), USA; Adam Duncan, NSWC Crane, USA; Kenneth A. LaBel, NASA/GSFC, USA; Matt Kay, Pat Bruner, Mike Krzesniak, NSWC Crane, USA; and Lei Dong, SCRIPPS Proton Therapy Center, USA</i>	
<b>TID and SEE Characterization of Microsemi's 4th Generation Radiation Tolerant RTG4 Flash-Based FPGA .....</b>	<b>211</b>
<i>Nadia Rezzak, Jih-Jong Wang, Durwyn Dsilva and Narayan Jat, Microsemi, USA</i>	
<b>SEE Tests of the NAND Flash Radiation Tolerant Intelligent Memory Stack.....</b>	<b>217</b>
<i>M. Bagatin, S. Gerardin, A. Paccagnella, DEI - University of Padova, Italy; C. Sellier, P. X. Wang, 3D PLUS, France; V. Ferlet-Cavrius and C. Poivey, ESA-ESTEC, Netherlands</i>	
<b>Single-Event Characterization of the 20 nm Xilinx Kintex UltraScale Field-Programmable Gate Array under Heavy Ion Irradiation .....</b>	<b>222</b>
<i>David S. Lee, Sandia National Laboratories, USA; Gregory R. Allen, NASA Jet Propulsion Laboratory, USA; Gary Swift, Swift Engineering and Radiation Services, LLC, USA; Matthew Cannon, Michael Wirthlin, Brigham Young University, USA; Jeffrey S. George, Rokutaro Koga, The Aerospace Corporation, USA; and Kangsen Huey, Xilinx Inc., USA</i>	
<b>Neutron, 64 MeV proton, thermal neutron and alpha single-event upset characterization of Xilinx 20nm UltraScale Kintex FPGA .....</b>	<b>228</b>
<i>Pierre Maillard, Michael Hart, Jeff Barton, Praful Jain and James Karp, Xilinx Inc., USA</i>	
<b>Cumulative Index.....</b>	<b>234</b>
<b>Author Index .....</b>	<b>262</b>